DIODES, SILICON, POWER RECTIFIER,

SCHOTTKY BARRIER,

BASED ON TYPE STPS1045

ESCC Detail Specification No. 5106/017

Issue 1

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DCR No.	CHANGE DESCRIPTION

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1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for Diodes, Silicon, Power Rectifier, Schottky Barrier, based on Type STPS1045. It shall be read in conjunction with ESCC Generic Specification No. 5000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type diodes specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The applicable derating information for the diodes specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein are shown in Figure 2.

1.6 FUNCTIONAL DIAGRAM

The functional diagram, showing lead identification of the diodes specified herein, is shown in Figure 3.

1.7 HIGH TEMPERATURE TEST PRECAUTIONS

For tin lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds +125°C shall be carried out in a 100% inert atmosphere.

2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

(a) ESCC Generic Specification No. 5000 for Discrete Semiconductors.

(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

TABLE 1(a) - TYPE VARIANTS

(1) VARIANT	(2) BASED ON TYPE	(3) CASE	(5) LEAD MATERIAL AND FINISH
01	STPS1045S	SMD.5	Q14
02	STPS1045CS	SMD.5	Q14

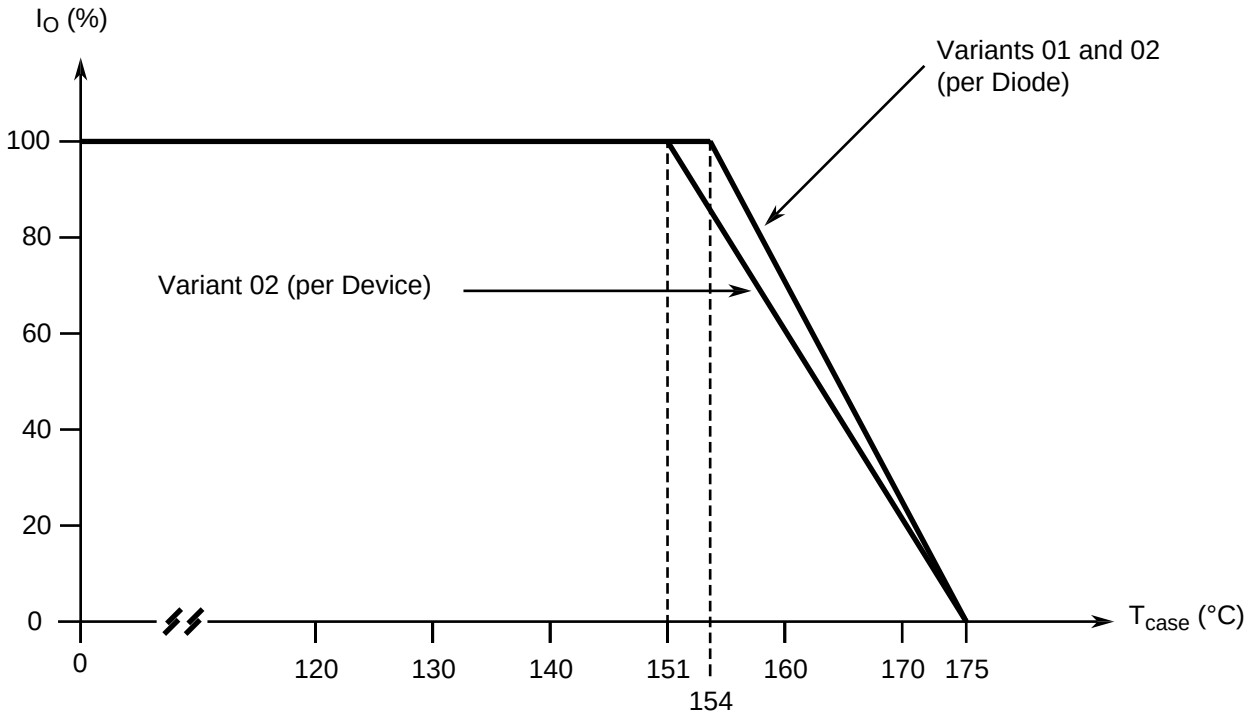
TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Forward Surge Current (per Diode)	I_{FSM}	200	A	Note 1
2	Repetitive Peak Reverse Voltage	V_{RRM}	45	V	
3	Repetitive Peak Reverse Current	I_{RRM}	1	A	Note 2
4	Average Output Rectified Current Variants 01 and 02 (per Diode) Variant 02 (per Device)	I_O	 10 20	A	50% duty cycle Note 3
5	RMS Forward Current (per Diode)	$I_{F(rms)}$	15	A	
6	Operating Temperature Range	T_{op}	-65 to +175	°C	
7	Storage Temperature Range	T_{stg}	-65 to +175	°C	
8	Soldering Temperature	T_{sol}	+245	°C	Note 4
9	Junction Temperature	T_J	+175	°C	
10	Thermal Resistance (Junction to Case) Variants 01 and 02 (per Diode) Variant 02 (per Device)	$R_{TH(J-C)}$	 2.8 1.6	°C/W	Notes 5, 6

NOTES

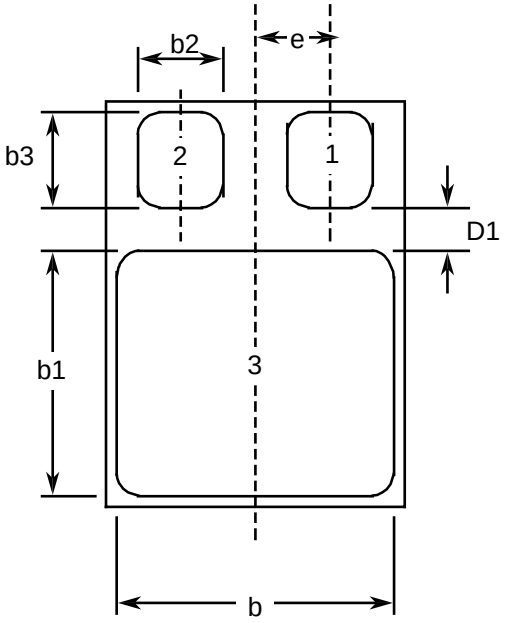
1. Sinusoidal pulse of 10ms duration.
2. Pulsed, duration 2µs, f=1kHz
3. At T_{case} = +151°C. For derating at T_{case} >+151°C, see Figure 1.
4. Duration 5 seconds maximum and the same package shall not be resoldered until 3 minutes have elapsed.
5. Package mounted on infinite heatsink.
6. The "per Device" ratings apply only when both anode terminals are tied together.

FIGURE 1 - PARAMETER DERATING INFORMATION

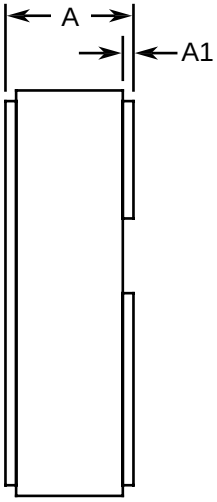


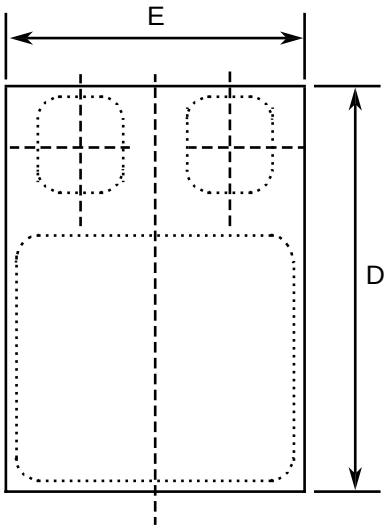
Average Output Rectified Current versus Temperature

FIGURE 2 - PHYSICAL DIMENSIONS



Bottom View





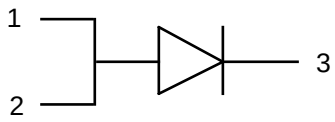
Top View

SYMBOL	MILLIMETRES	
	MIN.	MAX.
A	2.84	3.15
A1	0.25	0.51
b	7.13	7.39
b1	5.58	5.84
b2	2.28	2.54
b3	2.92	3.18
D	10.03	10.28
D1	0.76	-
E	7.39	7.64
e	1.91 Typical	

FIGURE 3 - FUNCTIONAL DIAGRAM

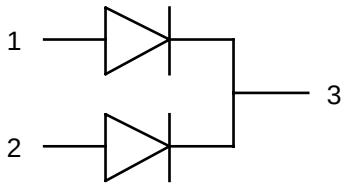
VARIANT 01

Terminal 1: Anode
Terminal 2: Anode
Terminal 3: Cathode



VARIANT 02

Terminal 1: Anode 1
Terminal 2: Anode 2
Terminal 3: Common Cathode



4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the diodes specified herein shall be as stated in this specification and ESCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Controls

None.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

(a) Para. 9.9.5, Safe Operating Area: Not applicable.

4.2.4 Deviations from Qualification Tests (Chart IV)

(a) Para. 9.15, Constant Acceleration: Not performed.

(b) Para. 9.19, Terminal Strength: Not applicable.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

(a) Para. 9.15, Constant Acceleration: Not performed.

(b) Para. 9.19, Terminal Strength: Not applicable.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the diodes specified herein shall be 2 grammes.

4.3.3 Terminal Strength

Not applicable.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

The case shall be hermetically sealed and have a ceramic body with a kovar lid.

4.4.2 Lead Material and Finish

The lead material shall be 'Q' with Type '14' finish in accordance with the requirements of ESCC Basic Specification No. 23500.

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with with the requirements of ESCC Basic Specification No. 21700 and the following paragraphs. When the component is too small to accommodate all of the marking specified, as much as space permits shall be marked and the marking information, in full, shall accompany the component in its primary package.

The information to be marked and the order of precedence, shall be as follows:-

(a) Lead Identification.

(b) The ESCC Component Number.

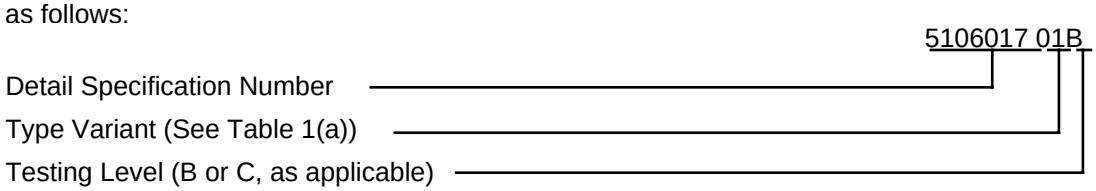
(c) Traceability Information.

4.5.2 Lead Identification

Cathode identification shall be as shown in Figures 2 and 3 of this specification.

4.5.3 The ESCC Component Number

Each component shall bear the ESCC Component Number which shall be constituted and marked as follows:



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at T_{amb}=+22±3 °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. Unless otherwise specified, the measurements in Table 3(a) shall be performed at T_{case}=+125(+0-5) °C and the measurement in Table 3(b) at T_{case}=-55(+5-0) °C.

4.6.3 Circuits for Electrical Measurements (Figure 4)

Not applicable.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at T_{amb}=+22±3 °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for High Temperature Reverse Bias Burn-in

The requirements for high temperature reverse bias burn-in are specified in Section 7 of ESCC Generic Specification No. 5000. The conditions for high temperature reverse bias burn-in shall be as specified in Table 5(a) of this specification.

4.7.3 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESCC Generic Specification No. 5000. The conditions for power burn-in shall be as specified in Table 5(b) of this specification.

4.7.4 Electrical Circuit for High Temperature Reverse Bias Burn-in (Figure 5(a))

Not applicable.

4.7.5 Electrical Circuit for Power Burn-in (Figure 5(b))

Not applicable.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - DC PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS (NOTE 1)	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current	I_R	4016	DC Method $V_R=V_{RWM}=45V$	-	100	µA
2	Forward Voltage Drop 1	V_{F1}	4011	I_F=3A (Note 2)	-	620	mV
3	Forward Voltage Drop 2	V_{F2}	4011	I_F=10A (Note 2)	-	750	mV
4	Forward Voltage Drop 3	V_{F3}	4011	I_F=20A (Note 2)	-	880	mV

NOTES
1. Measurements per each diode.
2. Pulsed measurement: Pulse Width≤300µs, Duty Cycle≤2%.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - AC PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS (NOTE 1)	LIMITS		UNIT
					MIN.	MAX.	
5	Junction Capacitance	C_J	4001	V_R=5V f=1MHz	-	500	pF
6	Thermal Impedance (Junction to Case)	$Z_{TH(J-C)}$	3101	I_H=15 to 40A t_H=50ms I_M=50mA t_{md}=100µs (Note 3)	(Calculate ΔV_F, see Note 2)		°C/W

NOTES
1. Measurements per each diode.
2. The limits for ΔV_F shall be defined by the manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the $R_{TH(J-C)}$ limits specified in Table 1(b).
3. During Chart II only, go-no-go.

TABLE 3(a) - ELECTRICAL MEASUREMENTS AT HIGH TEMPERATURE

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS (NOTE 1)	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current	I_R	4016	DC Method $V_R=V_{RWM}=45V$	-	15	mA
2	Forward Voltage Drop 1	V_{F1}	4011	I_F=3A (Note 2)	-	570	mV
3	Forward Voltage Drop 2	V_{F2}	4011	I_F=10A (Note 2)	-	700	mV
4	Forward Voltage Drop 3	V_{F3}	4011	I_F=20A (Note 2)	-	800	mV

NOTES
1. Measurements per each diode.
2. Pulsed measurement: Pulse Width≤300µs, Duty Cycle≤2%.

TABLE 3(b) - ELECTRICAL MEASUREMENTS AT LOW TEMPERATURE

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS (NOTE 1)	LIMITS		UNIT
					MIN.	MAX.	
3	Forward Voltage Drop 2	V_{F2}	4011	I_F=10A (Note 2)	-	850	mV

NOTES
1. Measurements per each diode.
2. Pulsed measurement: Pulse Width≤300μs, Duty Cycle≤2%.

FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

Not applicable.

TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMIT (Δ)	UNIT
1	Reverse Current	I_R	As per Table 2	As per Table 2	±25 or (1) ±100	μA %
2	Forward Voltage Drop 1	V_{F1}	As per Table 2	As per Table 2	±50	mV
4	Forward Voltage Drop 3	V_{F3}	As per Table 2	As per Table 2	±50	mV

NOTES
1. Whichever is greater, referred to the initial value.

TABLE 5(a) - CONDITIONS FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN

Not applicable.

TABLE 5(b) - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

No.	CHARACTERISTIC	SYMBOL	CONDITION	UNIT
1	Case Temperature	T_{case}	+125	°C
2	Reverse Voltage	V_R	36	V

FIGURE 5(a) - ELECTRICAL CIRCUIT FOR HIGH TEMPERATURE REVERSE BIAS BURN-IN

Not applicable.

FIGURE 5(b) - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TESTS

Not applicable.

4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESCC GENERIC SPECIFICATION NO. 5000)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. Unless otherwise stated, the measurements shall be performed at T_{amb}=+22±3 °C.

4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests

The parameters to be measured at intermediate points and on completion of endurance tests are scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at T_{amb}=+22±3 °C.

4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESCC Generic Specification No. 5000. The conditions for operating life testing shall be the same as specified in Table 5(b) for the power burn-in.

4.8.4 Electrical Circuit for Operating Life Tests (Figure 5(b))

Not applicable.

4.8.5 Conditions for High Temperature Storage Test (Part of Endurance Testing)

The requirements for the high temperature storage test are specified in Section 9 of ESCC Generic Specification No. 5000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.

TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current	I_R	As per Table 2	As per Table 2	-	100	µA
2	Forward Voltage Drop 1	V_{F1}	As per Table 2	As per Table 2	-	620	mV
3	Forward Voltage Drop 2	V_{F2}	As per Table 2	As per Table 2	-	750	mV
4	Forward Voltage Drop 3	V_{F3}	As per Table 2	As per Table 2	-	880	mV